5

CLAIMS

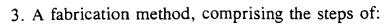
What is claimed is:

1	A 22	integrated	circuit	etmichire	comprising:
1.	$\Delta\Pi$	megrateu	CITCUIT	siructure,	comprising.

- NMOS and PMOS transistors, at least some of said PMOS transistors being formed in N-well diffusions in a semiconductor material; and
- a blanket P-type diffusion component having a peak concentration depth more than twice that of said p-well.
 - 2. An integrated circuit structure, comprising:
 - a first population of a first dopant in a semiconductor, said first population occupying a first region of said semiconductor;
 - a second population of said first dopant occupying a second region of said semiconductor, said second region being at a deeper implant depth than said first region;
 - a second dopant occupying said second region of said semiconductor;
- wherein said second dopant is of opposite electrical ionization than said first dopant.

Texas Instruments Page 10 TI-31408P

5



- a) implanting first dopant atoms into a semiconductor body to create a first-conductivity-type well diffusion therein; and
- b) implanting second dopant atoms into said semiconductor body, with more than twice the stopping distance and less than one-quarter of the dosage per unit area as said step a), to compensate atoms which channeled during said step a).

Texas Instruments Page 11 TI-31408P